MICRO ELECTRONICS

BC351

PNP SILICON TRANSISTOR

TO-92A

EBC

DESCRIPTION

BC351is PNP silicon planar transistor designed for AF small signal amplifier stages.

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	30V
Collector-Base Voltage	VCBO	40V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	100mA
Continuous Power Dissipation	Pd	300mW
Operating & Storage Junction Temperature	Tj,Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LVCEO	30		V	IC=1mA	IB=0
Collector-Base Breakdown Voltage	BVCBO	40		V	IC=100μA	IE=0
Emtter-Base Breakdown Voltage	BVEBO	5		V	IE=100μA	IC=0
Collector Cutoff Current	ICBO		100	nA	VCB=20V	IE=0
D.C. Current Gain	HFE	40	450		IC=2mA	VCE=5V
Group L		40	120		IC=2mA	VCE=5V
Group A		110	220		IC=2mA	VCE=5V
Group B		200	450		IC=2mA	VCE=5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.25	V	IC=10mA	IB=1mA
Output Capacitance	Cob		4	pF	VCB=10V	f=1MHz
Current Gain Bandwidth Product	fT	125		MHz	IC=5mA	VCE=10V
					f=100MHz	

* Pulse test : pulse width <300μS, duty cycle < 2%.

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

Aug-97